

8961726 TEXAS INSTR (OPTO)

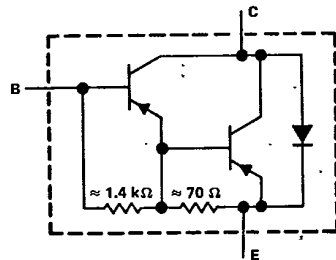
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BDX54, BDX54A, BDX54B, BDX54C
P-N-P SILICON POWER DARLINGTONS

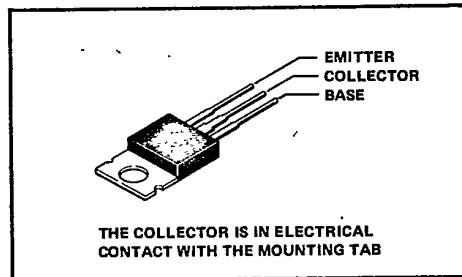
REVISED OCTOBER 1984

- 60 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Min hFE of 750 at 3 V, 3 A

device schematic



TO-220AB PACKAGE



3

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	BDX54	BDX54A	BDX54B	BDX54C
Collector-base voltage	-45 V	-60 V	-80 V	-100 V
Collector-emitter voltage (I _B = 0)	-45 V	-60 V	-80 V	-100 V
Emitter-base voltage			-5 V	
Continuous collector current			-8 A	
Continuous base current			-200 mA	
Continuous device dissipation at 25°C case temperature (see Note 1)			60 W	
Continuous device dissipation at 25°C free-air temperature (see Note 2)			2 W	
Operating free-air temperature range			-65°C to 150°C	
Operating collector junction and storage temperature range			-65°C to 150°C	

- NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.
 2. Derate linearly to 150°C free-air temperature at the rate of 16 mW/°C.

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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	BDX54		BDX54A		BDX54B		BDX54C		UNIT	
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP		MAX
V _{(BR)CEO}	I _C = -100 mA, I _B = 0, See Note 3	-45			-60			-80		-100	V
I _{CEO}	V _{CE} = -30 V, I _B = 0			-500		-500					μA
	V _{CE} = -40 V, I _B = 0							-500			
	V _{CE} = -50 V, I _B = 0									-500	
I _{CBO}	V _{CB} = -45 V, I _E = 0			-200							μA
	V _{CB} = -60 V, I _E = 0					-200					
	V _{CB} = -80 V, I _E = 0							-200			
	V _{CB} = -100 V, I _E = 0									-200	
I _{EBO}	V _{EB} = -5 V, I _C = 0			-2		-2		-2		-2	mA
h _{FE}	V _{CE} = -3 V, I _C = -3 A, See Notes 3 and 4	750			750			750		750	
V _{BE(sat)}	I _C = -3 A, I _B = -12 mA, See Notes 3 and 4			-2.5		-2.5		-2.5		-2.5	V
V _{CE(sat)}	I _C = -3 A, I _B = -12 mA, See Notes 3 and 4			-2		-2		-2		-2	V
V _F	I _F = 3 A			2.5		2.5		2.5		2.5	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_w = 300 \mu s$, duty cycle $\leq 2\%$.
 4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm (0.125 inch) from the device body.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
R _{θJC}			2.08	
R _{θJA}			62.5	°C/W

resistive-load switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{on}	I _C = -3 A, I _{B1} = -12 mA, I _{B2} = 12 mA,		1		μs
t _{off}	V _{BE(off)} = 4.2 V, R _L = 10 Ω, See Figure 1		5		

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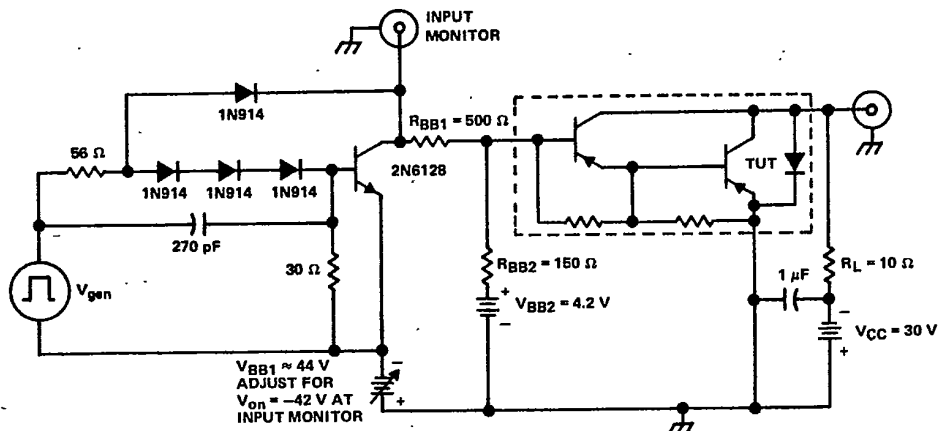
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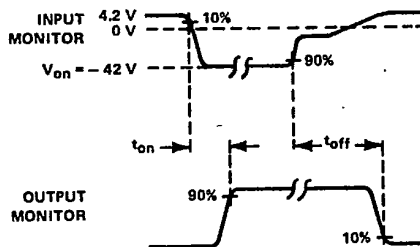
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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

- NOTES: A. V_{gen} is a 30-V pulse into a 50 Ω termination.
 B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r < 15$ ns, $t_f < 15$ ns, $Z_{out} = 50$ Ω , $t_w = 20$ μ s, duty cycle < 2 %.
 C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15$ ns, $R_{in} > 10$ M Ω , $C_{in} < 11.5$ pF.
 D. Resistors must be noninductive types.
 E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING



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TYPICAL CHARACTERISTICS

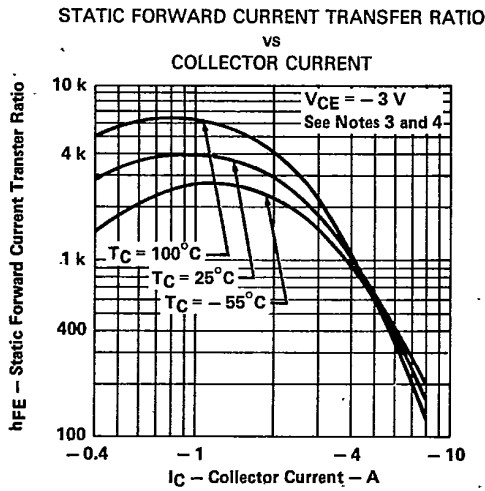


FIGURE 2

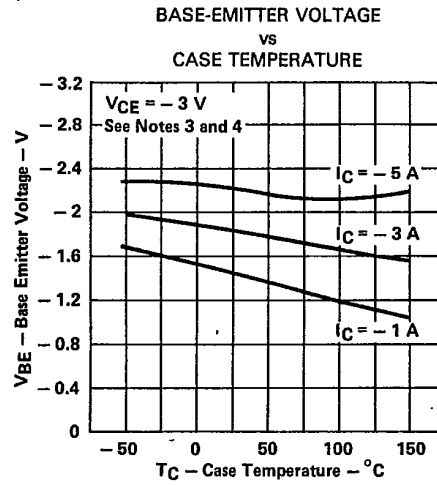


FIGURE 3

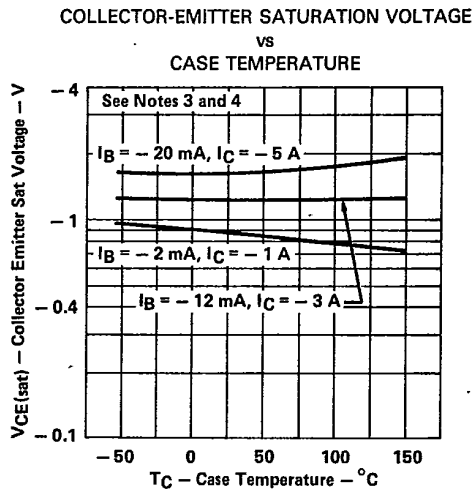


FIGURE 4

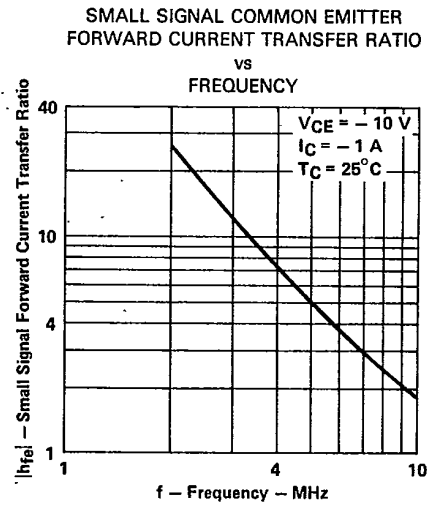


FIGURE 5

- NOTES: 3. These parameters must be measured using pulse techniques, $t_w = 300\mu s$, duty cycle $\leq 2\%$.
 4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3,2 mm (0.125 inch) from the device body.

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MAXIMUM SAFE OPERATING AREA
MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

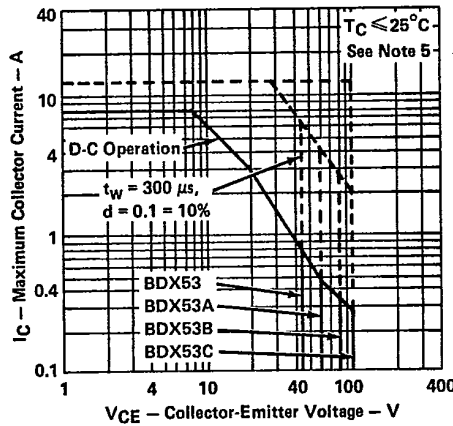


FIGURE 6

NOTE 5: This combination of maximum voltage and current may be achieved only when switching from saturation to cutoff with a clamped inductive load.

THERMAL INFORMATION

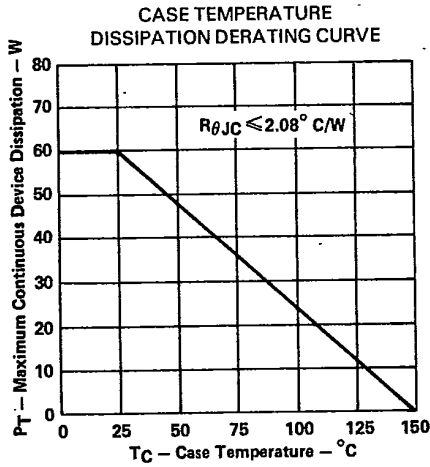


FIGURE 7

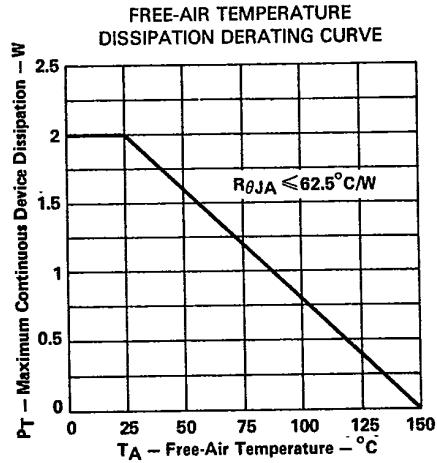


FIGURE 8



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